

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend paragraph 0017 starting at page 5, line 11, as follows:

[0017] In this storage on common system, a storage capacitor **50** is positioned at the center of a pixel area. The storage capacitor **50** should have a capacitance value large enough to maintain a stable pixel voltage. To this end, the storage capacitor **50** has a pixel electrode 55 electrically connected to a drain electrode 59, and a capacitor common electrode 45 having a gate insulating film 49 therebetween.

Please amend paragraph 0067 starting at page 15, line 24, as follows:

[0067] The protective layer 89 is formed by coating an insulating material by a spin coating technique to cover the source and drain electrodes 83 and 85. Accordingly, the surface of the protective layer **79 89** is flattened. In the protective layer **79 89** is formed the contact hole 90a which is patterned and in which the buffer metal layer 83b of the source electrode 83 is exposed.

Please amend paragraph 0068 starting at page 15, line 31, as follows:

[0068] The protective layer ~~79~~ 89 is formed of an organic insulating material, having a small dielectric constant, such as an acrylic organic compound, TEFLON (polytetrafluoroethylene), benzocyclobutene (BCB), CYTOP (perfluoropolymer resin), perfluorocyclobutane (PFCB), etc.